

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
-20V	80mΩ@-4.5V	-3A
	100mΩ@-2.5V	

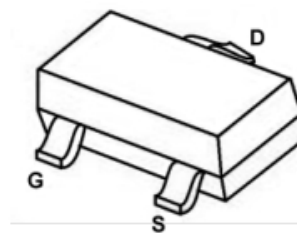
## Feature

- TrenchFET Power MOSFET
- Excellent  $R_{DS(on)}$  and Low Gate Charge

## Applications

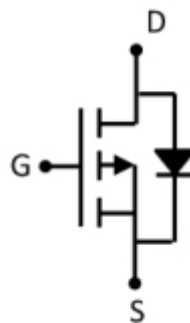
- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

## Package

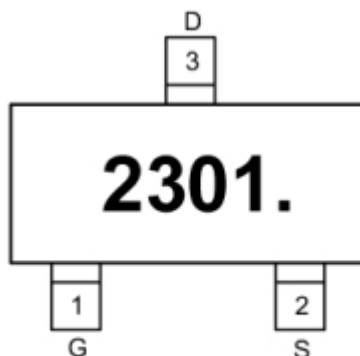


SOT-23

## Circuit diagram



## Marking



**2301. =Device Code**

## Absolute maximum ratings

(T<sub>a</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Continuous Drain Current	I <sub>D</sub>	-3	A
Pulsed Drain Current	I <sub>DM</sub>	-12	A
Power Dissipation <sup>1)</sup>	P <sub>D</sub>	0.9	W
Thermal Resistance from Junction to Ambient	R <sub>θJA</sub>	130	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~ +150	°C

## Electrical characteristics

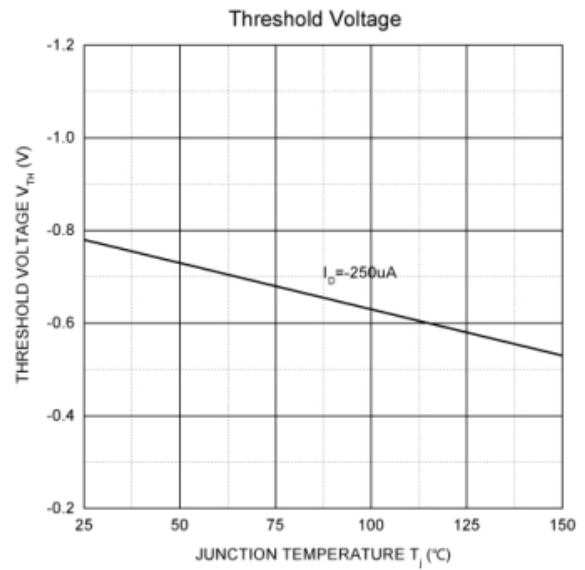
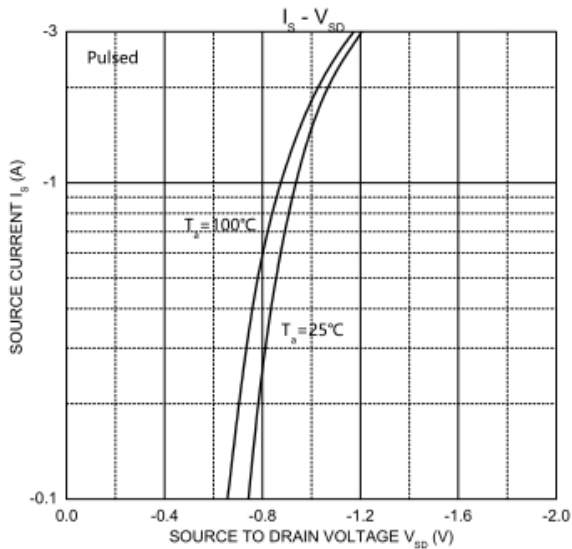
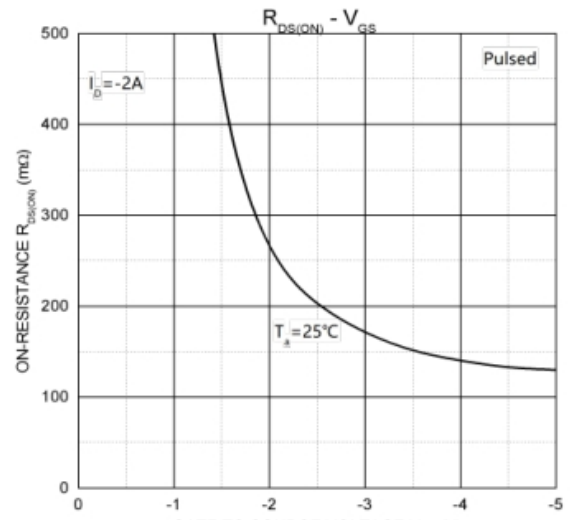
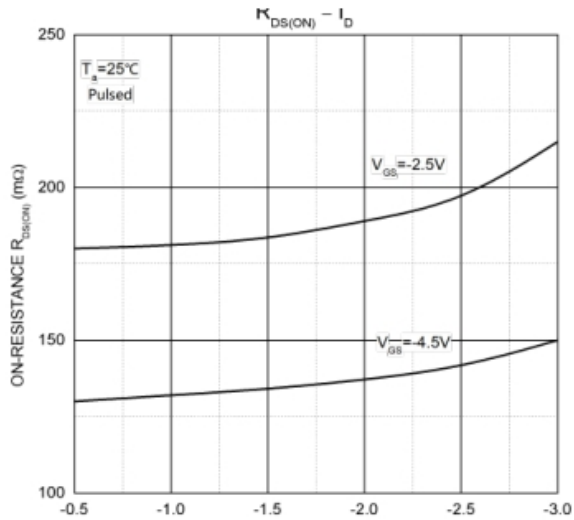
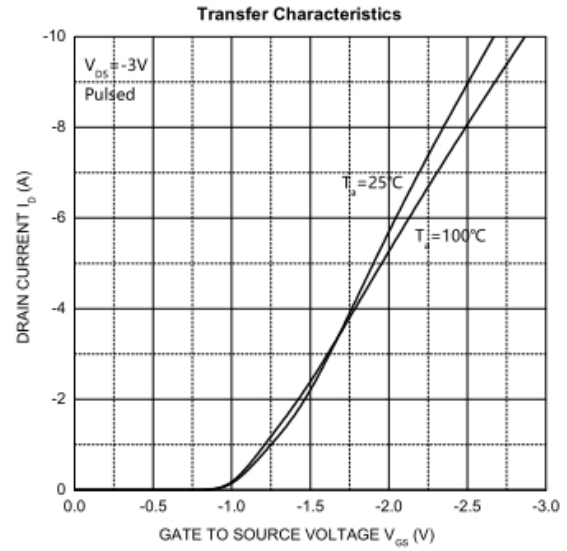
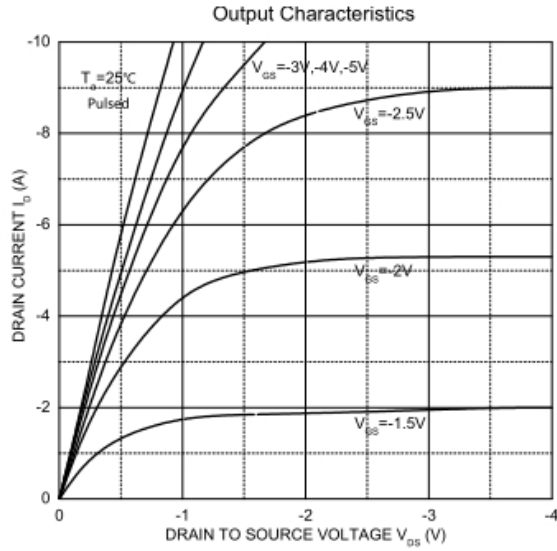
( $T_A=25^{\circ}\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$BV_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -16V, V_{GS} = 0V$			-1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0V$			$\pm 100$	$\mu A$
Gate threshold voltage <sup>(1)</sup>	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.5	-0.7	-1	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -4A$		80	110	m $\Omega$
		$V_{GS} = -2.5V, I_D = -2A$		100	140	
Dynamic Characteristics						
Input capacitance	$C_{iss}$	$V_{DS} = -10V, V_{GS} = 0V,$ $f = 1MHz$		405		pF
Output capacitance	$C_{oss}$			75		
Reverse transfer capacitance	$C_{rss}$			55		
Total Gate Charge	$Q_g$	$V_{DS} = -10V, V_{GS} = -2.5V,$ $I_D = -3A$		3.3	12	nC
Gate-Source Charge	$Q_{gs}$			0.7		
Gate-Drain Charge	$Q_{gd}$			1.3		
Turn-on Delay Time	$T_{d(on)}$	$V_{DD} = -10V, V_{GEN} = -4.5V,$ $I_D = -1A, R_L = 10\Omega,$ $R_{GEN} = 1\Omega$		11		nS
Turn-on Rise Time	$T_r$			35		
Turn-Off Delay Time	$T_{d(off)}$			30		
Turn-Off Fall Time	$t_f$			10		
Source-Drain Diode Characteristics						
Body Diode Voltage	$V_{DS}$	$I_S = -1.25A, V_{GS} = 0V$		-0.8	-1.3	V

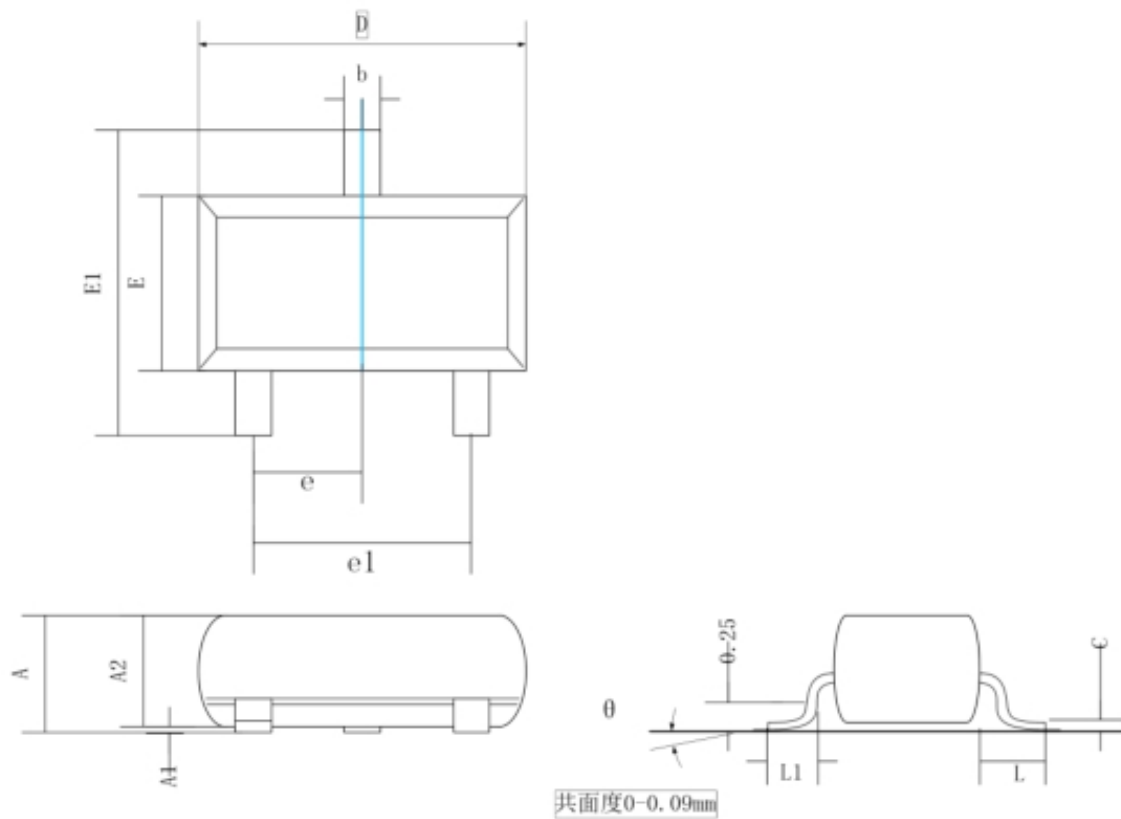
### Notes:

1. Pulse Test: Pulse Width < 300 $\mu s$ , Duty Cycle  $\leq 2\%$ .
2. Guaranteed by design, not subject to production testing.

## Typical Characteristics



## SOT-23 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50
$\theta$	0°	8°